

**ELECTRO-LUMINESCENCE DEVICE INCLUDING A THIN
FILM TRANSISTOR AND METHOD OF FABRICATING AN
ELECTRO-LUMINESCENCE DEVICE**

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ABSTRACT OF THE DISCLOSURE

An electro-luminescence device including an electro-luminescence
element and a thin film transistor electrically connected to the electro-
luminescence element. The thin film transistor includes a gate electrode
formed over a substrate, an insulating layer formed over the gate electrode,
10 and a first semiconductor pattern formed over the insulating layer. An etch
stop layer is formed over the first semiconductor layer. A second
semiconductor pattern is formed over the etch stop layer at one side of the
etch stop layer, and a third semiconductor pattern is formed over the etch stop
layer at another side of the etch stop layer. A source electrode is formed over
15 the second semiconductor pattern, and a drain electrode is formed over the
third semiconductor pattern.